

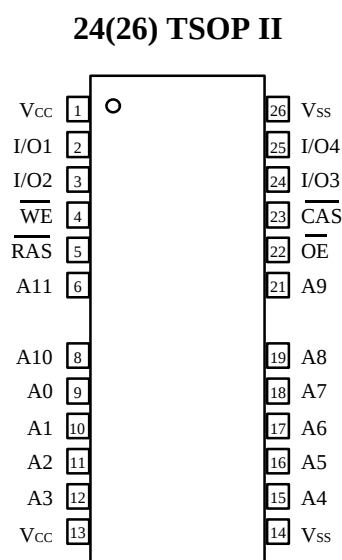
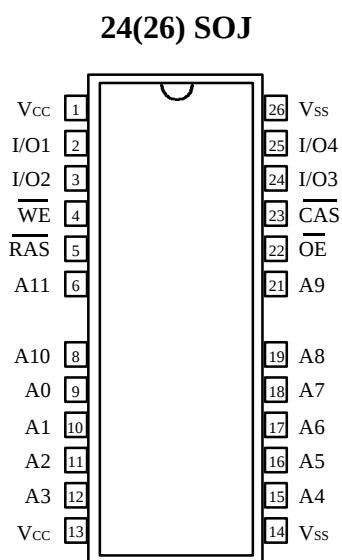


GM71V16400C
GM71VS16400CL
4,194,304 WORDS x 4 BIT
CMOS DYNAMIC RAM

Description

The GM71V(S)16400C/CL is the new generation dynamic RAM organized 4,194,304 words x 4 bit. GM71V(S)16400C/CL has realized higher density, higher performance and various functions by utilizing advanced CMOS process technology. The GM71V(S)16400C/CL offers Fast Page Mode as a high speed access mode. Multiplexed address inputs permit the GM71V(S)16400C/CL to be packaged in a standard 300 mil 24(26) pin SOJ, and a standard 300 mil 24(26) pin plastic TSOP II. The package size provides high system bit densities and is compatible with widely available automated testing and insertion equipment. System oriented features include single power supply 3.3V+/-0.3V tolerance, direct interfacing capability with high performance logic families such as Schottky TTL.

Pin Configuration



(Top View)

Features

- * 4,194,304 Words x 4 Bit Organization
 - * Fast Page Mode Capability
 - * Single Power Supply (3.3V+/-0.3V)
 - * Fast Access Time & Cycle Time
- (Unit: ns)

	t _{RAC}	t _{CAC}	t _{RC}	t _{PC}
GM71V(S)16400C/CL-5	50	13	90	35
GM71V(S)16400C/CL-6	60	15	110	40
GM71V(S)16400C/CL-7	70	18	130	45

- * Low Power
 - Active : 324/288/252mW (MAX)
 - Standby : 7.2mW (CMOS level : MAX)
 - : 0.36mW (L-version : MAX)
- * RAS Only Refresh, CAS before RAS Refresh, Hidden Refresh Capability
- * All inputs and outputs TTL Compatible
- * 4096 Refresh Cycles/64ms
- * 4096 Refresh Cycles/128ms (L-version)
- * Self Refresh Operation (L-version)
- * Battery backup operation (L-version)
- * Test function : 16bit parallel test mode



Pin Description

Pin	Function	Pin	Function
A0-A11	Address Inputs	$\overline{WE}$	Read/Write Enable
A0-A11	Refresh Address Inputs	$\overline{OE}$	Output Enable
I/O1-I/O4	Data Input/Data Output	V _{CC}	Power (+3.3V)
$\overline{RAS}$	Row Address Strobe	V _{SS}	Ground
$\overline{CAS}$	Column Address Strobe	NC	No Connection

Ordering Information

Type No.	Access Time	Package
GM71V(S)16400CJ/CLJ-5 GM71V(S)16400CJ/CLJ-6 GM71V(S)16400CJ/CLJ-7	50ns 60ns 70ns	300 Mil 24(26) Pin Plastic SOJ
GM71V(S)16400CT/CLT-5 GM71V(S)16400CT/CLT-6 GM71V(S)16400CT/CLT-7	50ns 60ns 70ns	300 Mil 24(26) Pin Plastic TSOP II

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
T _A	Ambient Temperature under Bias	0 ~ 70	C
T _{STG}	Storage Temperature	-55 ~ 125	C
V _{IN/OUT}	Voltage on any Pin Relative to V _{SS}	-0.5 ~ V _{CC} +0.5(<=4.6V(MAX))	V
V _{CC}	Supply Voltage Relative to V _{SS}	-0.5 ~ 4.6	V
I _{OUT}	Short Circuit Output Current	50	mA
P _D	Power Dissipation	1.0	W

Recommended DC Operating Conditions (T_A = 0 ~ 70C)

Symbol	Parameter	Min	Typ	Max	Unit
V _{CC}	Supply Voltage	3.0	3.3	3.6	V
V _{IH}	Input High Voltage	2.0	-	V _{CC} +0.3	V
V _{IL}	Input Low Voltage	-0.3	-	0.8	V

Note: All voltage referred to V_{SS}.

DC Electrical Characteristics ($V_{CC} = 3.3V \pm 0.3V$, $V_{SS} = 0V$, $T_A = 0 \sim 70^\circ C$)

Symbol	Parameter	Min	Max	Unit	Note
V_{OH}	Output Level Output "H" Level Voltage ($I_{OUT} = -2mA$)	2.4	V_{CC}	V	
V_{OL}	Output "L" Level Voltage ($I_{OUT} = 2mA$)	0	0.4	V	
I_{CC1}	Operating Current Average Power Supply Operating Current (RAS, CAS Cycling : $t_{RC} = t_{RC \min}$)	50ns	-	90	mA
		60ns	-	80	
		70ns	-	70	
I_{CC2}	Standby Current (TTL) Power Supply Standby Current ($\overline{RAS}, \overline{CAS}, D = High-Z$)	-	2	mA	
I	Average Power Supply Current RAS Only Refresh Mode ($t = t_{min}$)	50ns	-	90	mA
		60ns	-	80	
		70ns	-	70	
	Fast Page Mode Current Fast Page Mode ($t_{PC} = t_{PC \min}$)	50ns	-	80	1, 3
		60ns	-	70	
		70ns	-	60	
I_{CC5}	Power Supply Standby Current (RAS, CAS $\geq V_{CC} - 0.2V$, DOUT = High-Z)	-	-	mA	4
		-	100	uA	
I_{CC6}	CAS-before-RAS Refresh Current ($t = t_{min}$)	ns	-	90	mA
		60	-	-	
		70ns	-	70	
	Battery Backup Operating Current(Standby with CBR Refresh) (CBR refresh, $t_{RC} = 31.3\mu s$, $t_{RAS} \leq 0.3\mu s$, DOUT = High-Z, CMOS interface)	-	-	uA	
I	Standby Current $\overline{RAS} = V_{IH}$ $\overline{CAS} = V_{IL}$ DOUT = Enable		5		1
	Self-Refresh Mode Current (RAS, CAS $\leq 0.2V$, DOUT = High-Z, CMOS interface)		200	uA	
$I_{L(I)}$	Input Leakage Current Any Input ($0V \leq V_{IN} \leq 4.6V$)	-10	10	uA	
$I_{L(O)}$	(D is Disabled, $0V \leq V_{IN} \leq 4.6V$)		10	uA	

Note: 1. I

I

2. Address can be changed once or less while $\overline{RAS} = V$

3. Address can be changed once or less while CAS = V

4. L - Version.



GM71V16400C GM71VS16400CL

Capacitance ($V_{CC} = 3.3V \pm 0.3V$, $T_A = 25^\circ C$)

Symbol	Parameter	Min	Max	Unit	Note
C _{I1}	Input Capacitance (Address)	-	5	pF	1
C _{I2}	Input Capacitance (Clocks)	-	7	pF	1
C _{I/O}	Output Capacitance (Data-In/Out)	-	7	pF	1, 2

Note: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.

2. CAS = V_{IH} to disable D_{OUT}.

AC Characteristics ($V_{CC} = 3.3V \pm 0.3V$, $V_{SS} = 0V$, $T_A = 0 \sim 70^\circ C$, Notes 1, 2, 3, 19, 20)

Test Conditions

Input rise and fall times : 2ns

Input timing reference levels : 0.8V, 2.0V

Output timing reference levels : 0.8V, 2.0V

Output load : 1 TTL gate + C_L (100pF)

(Including scope and jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common Parameters)

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{RC}	Random Read or Write Cycle Time	90	-	110	-	130	-	ns	
t _{RP}	$\overline{RAS}$ Precharge Time	30	-	40	-	50	-	ns	
t _{CP}	$\overline{CAS}$ Precharge Time	8	-	10	-	10	-	ns	
t _{RAS}	$\overline{RAS}$ Pulse Width	50	10,000	60	10,000	70	10,000	ns	
t _{CAS}	$\overline{CAS}$ Pulse Width	13	10,000	15	10,000	18	10,000	ns	
t _{ASR}	Row Address Set up Time	0	-	0	-	0	-	ns	
t _{RAH}	Row Address Hold Time	8	-	10	-	10	-	ns	
t _{ASC}	Column Address Set-up Time	0	-	0	-	0	-	ns	
t _{CAH}	Column Address Hold Time	8	-	10	-	15	-	ns	
t _{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay Time	18	45	20	45	20	52	ns	4
t _{RAD}	$\overline{RAS}$ to Column Address Delay Time	13	30	15	30	15	35	ns	5
t _{RSH}	$\overline{RAS}$ Hold Time	13	-	15	-	18	-	ns	
t _{CSH}	$\overline{CAS}$ Hold Time	50	-	60	-	70	-	ns	
t _{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	5	-	5	-	5	-	ns	
t _{ODD}	$\overline{OE}$ to D _{IN} Delay Time	13	-	15	-	18	-	ns	6
t _{DZO}	$\overline{OE}$ Delay Time from D _{IN}	0	-	0	-	0	-	ns	7
t _{DZC}	$\overline{CAS}$ Delay Time from D _{IN}	0	-	0	-	0	-	ns	7
t _T	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	8

Read Cycle

Symbol		GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{RAC}	Access Time from $\overline{\text{RAS}}$	-	50	-	60	-	70	ns	9,10,21
t _{CAC}	Access Time from $\overline{\text{CAS}}$	-	13	-	15	-	18	ns	10,11, 18,21
t _{AA}	Access Time from Address	-	25	-	30	-	35	ns	10,12, 18,21
t _{OAC}	Access Time from $\overline{\text{OE}}$	-	13	-	15	-	18	ns	10
t _{RCS}	Read Command Setup Time	0	-	0	-	0	-	ns	
t _{RCH}	Read Command Hold Time to $\overline{\text{CAS}}$	0	-	0	-	0	-	ns	13
t _{RRH}	Read Command Hold Time to $\overline{\text{RAS}}$	5	-	5	-	5	-	ns	13
t _{RAL}	Column Address to $\overline{\text{RAS}}$ Lead Time	25	-	30	-	35	-	ns	
t _{CAL}	Column Address to $\overline{\text{CAS}}$ Lead Time	25	-	30	-	35	-	ns	
t _{CLZ}	$\overline{\text{CAS}}$ to Output in low-Z	0	-	0	-	0	-	ns	
t _{OH}	Output Data Hold Time	3	-	3	-	3	-	ns	
t _{OH0}	Output Data Hold Time from $\overline{\text{OE}}$	3	-	3	-	3	-	ns	
t _{OEZ}	Output Buffer Turn-off Time to $\overline{\text{OE}}$	-	13	-	15	-	15	ns	14
t _{OFF}	Output Buffer Turn-off Time	-	13	-	15	-	15	ns	14
t _{CDD}	$\overline{\text{CAS}}$ to D _{IN} Delay Time	13	-	15	-	18	-	ns	6

Write Cycle

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{WCS}	Write Command Setup Time	0	-	0	-	0	-	ns	15
t _{WCH}	Write Command Hold Time	8	-	10	-	15	-	ns	
t _{WP}	Write Command Pulse Width	8	-	10	-	10	-	ns	
t _{RWL}	Write Command to $\overline{\text{RAS}}$ Lead Time	13	-	15	-	18	-	ns	
t _{CWL}	Write Command to $\overline{\text{CAS}}$ Lead Time	13	-	15	-	18	-	ns	
t _{DS}	Data-in Setup Time	0	-	0	-	0	-	ns	16
t _{DH}	Data-in Hold Time	8	-	10	-	15	-	ns	16

Read- Modify-Write Cycle

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{RWC}	Read-Modify-Write Cycle Time	131	-	155	-	181	-	ns	
t _{RWD}	RAS to $\overline{\text{WE}}$ Delay Time	73	-	85	-	98	-	ns	15
t _{CWD}	CAS to $\overline{\text{WE}}$ Delay Time	36	-	40	-	46	-	ns	15
t _{AWD}	Column Address to $\overline{\text{WE}}$ Delay Time	48	-	55	-	63	-	ns	15
t _{OE}	OE Hold Time from $\overline{\text{WE}}$	13	-	15	-	18	-	ns	

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{CSR}	$\overline{\text{CAS}}$ Setup Time (CAS-before-RAS Refresh Cycle)	5	-	5	-	5	-	ns	
t _{CHR}	$\overline{\text{CAS}}$ Hold Time (CAS-before-RAS Refresh Cycle)	8	-	10	-	10	-	ns	
t _{WRP}	$\overline{\text{WE}}$ Setup Time (CAS-before-RAS Refresh Cycle)	0	-	0	-	0	-	ns	
t _{WRH}	$\overline{\text{WE}}$ Hold Time (CAS-before-RAS Refresh Cycle)	10	-	10	-	10	-	ns	
t _{RPC}	RAS Precharge to $\overline{\text{CAS}}$ Hold Time	5	-	5	-	5	-	ns	

Fast Page Mode Cycle

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{PC}	Fast Page Mode Cycle Time	35	-	40	-	45	-	ns	
t _{RASP}	Fast Page Mode $\overline{\text{RAS}}$ Pulse Width	-	100,000	-	100,000	-	100,000	ns	17
t _{ACP}	Access Time from $\overline{\text{CAS}}$ Precharge	-	30	-	35	-	40	ns	10,18,21
t _{RHCP}	$\overline{\text{RAS}}$ Hold Time from $\overline{\text{CAS}}$ Precharge	30	-	35	-	40	-	ns	



Fast Page Mode Read-Modify-Write Cycle

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{PRWC}	Fast Page Mode Read-Modify-Write Cycle Time	76	-	85	-	96	-	ns	
t _{CPW}	$\overline{\text{WE}}$ Delay Time from $\overline{\text{CAS}}$ Precharge	53	-	60	-	68	-	ns	15

Test Mode Cycle *20

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{WTS}	Test Mode $\overline{\text{WE}}$ Setup Time	0	-	0	-	0	-	ns	
t _{WTH}	Test Mode $\overline{\text{WE}}$ Hold Time	10	-	10	-	10	-	ns	

Refresh

Symbol	Parameter	GM71V(S)16400 C/CL-5		GM71V(S)16400 C/CL-6		GM71V(S)16400 C/CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{REF}	Refresh Period	-	64	-	64	-	64	ms	4096 cycles
t _{REF}	Refresh Period (L - version)	-	128	-	128	-	128	ms	4096 cycles

Self Refresh Mode (L-version)

Symbol	Parameter	GM71VS16400 CL-5		GM71VS16400 CL-6		GM71VS16400 CL-7		Unit	Note
		Min	Max	Min	Max	Min	Max		
t _{RASS}	$\overline{\text{RAS}}$ Pulse Width(Self-Refresh)	100	-	100	-	100	-	us	
t _{RPS}	$\overline{\text{RAS}}$ Precharge Time(Self-Refresh)	90	-	110	-	130	-	ns	
t _{CHS}	$\overline{\text{CAS}}$ Hold Time(Self-Refresh)	-50	-	-50	-	-50	-	ns	

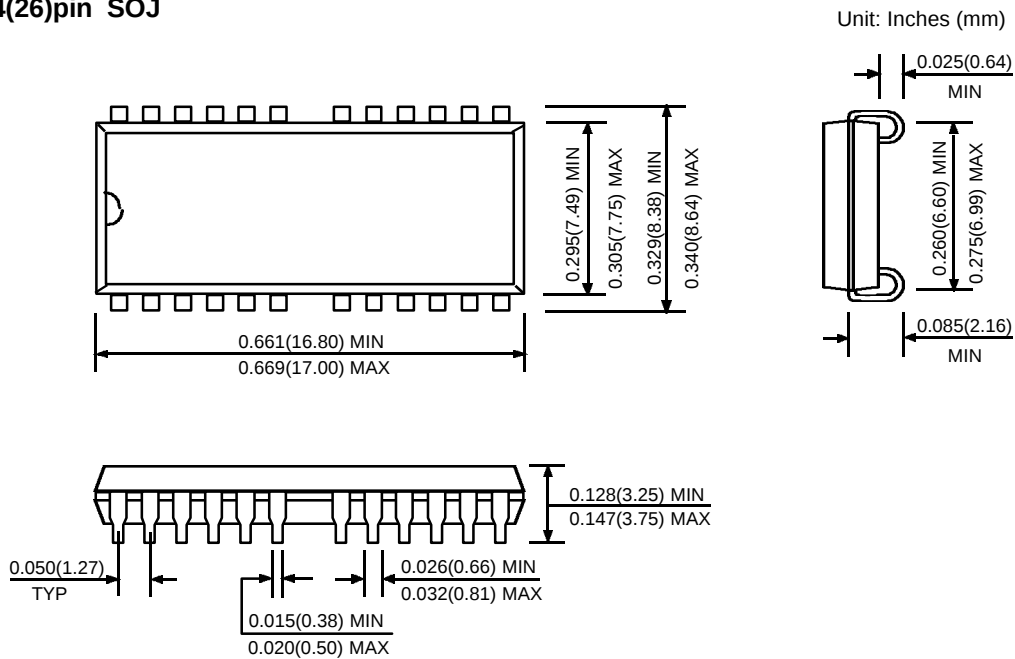
Notes:

1. AC Measurements assume $t_r = 5\text{ns}$.
2. initialization cycles (any combination of cycles containing $\overline{\text{RAS}}$ -only refresh or $\overline{\text{CAS}}$ -before-RAS refresh). If the internal refresh counter is used, a minimum of eight $\overline{\text{CAS}}$ -before-RAS
3. Only row address is indispensable on address A10 and A11.
4. Operation with the $t_{\text{RCD}}(\text{max})$ limit insures that $t_{\text{RAC}}(\text{max})$ can be met, $t_{\text{RCD}}(\text{max})$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{\text{RCD}}(\text{max})$ limit, then access time is controlled exclusively by t_{CAC} .
5. Operation with the $t_{\text{RAD}}(\text{max})$ limit insures that $t_{\text{RAC}}(\text{max})$ can be met, $t_{\text{RAD}}(\text{max})$ is specified as a reference point only; if t_{RAD} is greater than the specified $t_{\text{RAD}}(\text{max})$ limit, then access time is controlled exclusively by t_{AA} .
6. Either t_{ODD} or t_{CDD} must be satisfied.
7. Either t_{DZO} or t_{DZC} must be satisfied.
8. $V_{\text{IH}}(\text{min})$ and $V_{\text{IL}}(\text{max})$ are reference levels for measuring timing of input signals. Also, transition times are measured between $V_{\text{IH}}(\text{min})$ and $V_{\text{IL}}(\text{max})$.
9. Assume that $t_{\text{RCD}} \leq t_{\text{RCD}}(\text{max})$ and $t_{\text{RAD}} \leq t_{\text{RAD}}(\text{max})$. If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
10. Measured with a load circuit equivalent to 1 TTL loads and 100pF. ($V_{\text{OH}} = 2.0\text{V}$, $V_{\text{OL}} = 0.8\text{V}$)
11. Assume that $t_{\text{RCD}} \geq t_{\text{RCD}}(\text{max})$ and $t_{\text{RCD}} + t_{\text{CAC}}(\text{max}) \geq t_{\text{RAD}} + t_{\text{AA}}(\text{max})$.
12. Assume that $t_{\text{RAD}} \geq t_{\text{RAD}}(\text{max})$ and $t_{\text{RCD}} + t_{\text{CAC}}(\text{max}) \leq t_{\text{RAD}} + t_{\text{AA}}(\text{max})$.
13. Either t_{RCH} or t_{RRH} must be satisfied for a read cycles.
14. $t_{\text{OFF}}(\text{max})$ and $t_{\text{OEZ}}(\text{max})$ define the time at which the outputs achieve the open circuit condition and are not referenced to output voltage levels.
15. t_{WCS} , t_{RWd} , t_{CWD} , t_{AWD} and t_{CPW} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{\text{WCS}} \geq t_{\text{WCS}}(\text{min})$, the cycles is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{\text{RWd}} \geq t_{\text{RWd}}(\text{min})$, $t_{\text{CWD}} \geq t_{\text{CWD}}(\text{min})$, and $t_{\text{AWD}} \geq t_{\text{AWD}}(\text{min})$, or $t_{\text{CWD}} \geq t_{\text{CWD}}(\text{min})$, $t_{\text{AWD}} \geq t_{\text{AWD}}(\text{min})$ and $t_{\text{CPW}} \geq t_{\text{CPW}}(\text{min})$, the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
16. These parameters are referenced to $\overline{\text{CAS}}$ leading edge in early write cycles and to $\overline{\text{WE}}$ leading edge in delayed write or read-modify-write cycles.
17. t_{RASP} defines $\overline{\text{RAS}}$ pulse width in Fast page mode cycles.
18. Access time is determined by the longest among t_{AA} or t_{CAC} or t_{ACP} .

19. In delayed write or read-modify-write cycles, $\overline{\text{OE}}$ must disable output buffer prior to applying data to the device. After $\overline{\text{RAS}}$ is reset, if $t_{\text{OE}} \geq t_{\text{CWL}}$, the I/O pin will remain open circuit (high impedance); if $t_{\text{OE}} < t_{\text{CWL}}$, invalid data will be out at each I/O.
20. The 16M DRAM offers a 16-bit time saving parallel test mode. Address $\overline{\text{CA0}}$ and $\overline{\text{CA1}}$ for the $4\text{M} \times 4$ are don't care during test mode. Test mode is set by performing a $\overline{\text{WE}}$ -and- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ (WCBR) cycle. In 16-bit parallel test mode, data is written into 4 bits in parallel at each I/O ($\overline{\text{I/O1}}$ to $\overline{\text{I/O4}}$) and read out from each I/O. If 4 bits of each I/O are equal (all 1s or 0s), data output pin is a high state during test mode read cycle, then the device has passed. If they are not equal, data output pin is a low state, then the device has failed. Refresh during test mode operation can be performed by normal read cycles or by WCBR refresh cycles. To get out of test mode and enter a normal operation mode, perform either a regular $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle or $\overline{\text{RAS}}$ -only refresh cycle.
21. In a test mode read cycle, the value of t_{RAC} , t_{AA} , t_{CAC} and t_{ACP} is delayed by 2ns to 5ns for the specified value. These parameters should be specified in test mode cycles by adding the above value to the specified value in this data sheet.

Package Dimension

24(26)pin SOJ



24(26)pin TSOP-II

